

SDRAM Addressing

The table below shows addressing for the 4Gb die density. Where applicable, a distinction is made between perchannel and per-die parameters. All bank, row, and column addresses are shown per-channel.

Table 2: Device Addressing

Configuration		128M32 (4Gb)
Die per package Device density (per die)		1 4Gb
Configuration		16Mb x 16 DQ x 8 banks x 2 channels x 1 rank
Number of channels (per die)		2
Number of ranks per channel		1
Number of banks (per channel)		8
Array prefetch (bits) (per channel)		256
Number of rows (per bank)		16,384
Number of columns (fetch boundaries)		64
Page size (bytes)		2048
Channel density (bits per channel)		2,147,483,648
Total density (bits per die)		4,294,967,296
Bank address		BA[2:0]
x16	Row addresses	R[13:0]
	Column addresses	C[9:0]
Burst starting address boundary	'	64-bit

- Notes: 1. The lower two column addresses (C0–C1) are assumed to be zero and are not transmitted on the CA bus.
 - 2. Row and column address values on the CA bus that are not used for a particular density are "Don't Care."
 - 3. For non-binary memory densities, only half of the row address space is valid. When the MSB address bit is HIGH, the MSB - 1 address bit must be LOW.

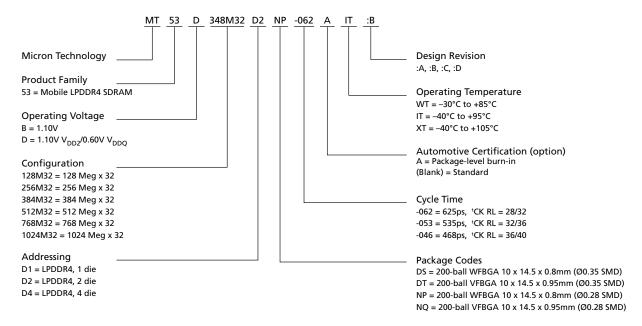


Part Number and Part Marking Information

Part Number Ordering

Micron LPDDR4 devices are available in different configurations and densities. Verify valid part numbers by using Micron's part catalog search at www.micron.com. To compare features and specifications by device type, visit www.micron.com/products. Contact the factory for devices not found.

Figure 1: Part Number Chart



FBGA Part Marking Decoder

Due to space limitations, FBGA-packaged components have an abbreviated part marking that is different from the part number. Micron's FBGA part marking decoder is available at www.micron.com/decoder.

Full specification can be acquired through a Micron representative and under NDA